查询BD905供应商 捷多邦，专业PCB打样工厂，24小时加急出货

MOSPEC

COMPLEMENTARY SILICON PLASTIC POWER TRANSISTORS

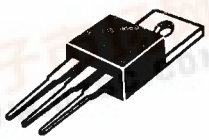
... designed for use in general purpose power amplifier and switching applications.

NPN	PNP
BD905	BD906
BD907	BD908
BD909	BD910
BD911	BD912

15 AMPERE
COMPLEMENTARY SILICON
POWER TRANSISTORS
45 -100 VOLTS
90 WATTS

FEATURES:

* Collector-Emitter Sustaining Voltage -
  $V_{CEO(sus)}$= 45V(Min)- BD905, BD906
  60V(Min)- BD907, BD908
  80V(Min)- BD909, BD910
  100V(Min)- BD911, BD912
* DC Current Gain hFE= 40(Min)@I_C= 0.5A
* Current Gain-Bandwidth Product fT=3.0 MHz (Min)@ I_C=500mA



TO-220

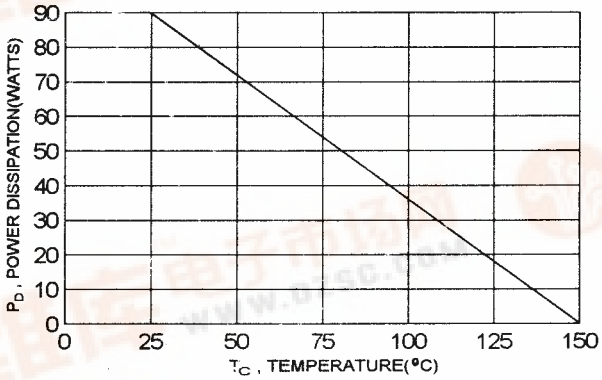
MAXIMUM RATINGS

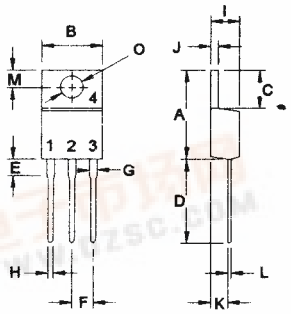
Characteristic	Symbol	BD905 BD906	BD907 BD908	BD909 BD910	BD911 BD912	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	100	V
Collector-Base Voltage	V_{CBO}	45	60	80	100	V
Emitter-Base Voltage	V_{EBO}	5.0				V
Collector Current - Continuous - Peak	I_C	15 20				A
Base Current	I_B	5.0				A
Total Power Dissipation@T_C = 25°C Derate above 25°C	P_D	90 0.72				W W/°C
Operating and Storage Junction Temperature Range	T_J,T_{STG}	-65 to +150				°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	Rθjc	1.38	°C/W

FIGURE -1 POWER DERATING





PIN 1.BASE
2.COLLECTOR
3.EMITTER
4.COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	14.68	15.31
B	9.78	10.42
C	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.20	2.97
L	0.33	0.55
M	2.48	2.98
O	3.70	3.90

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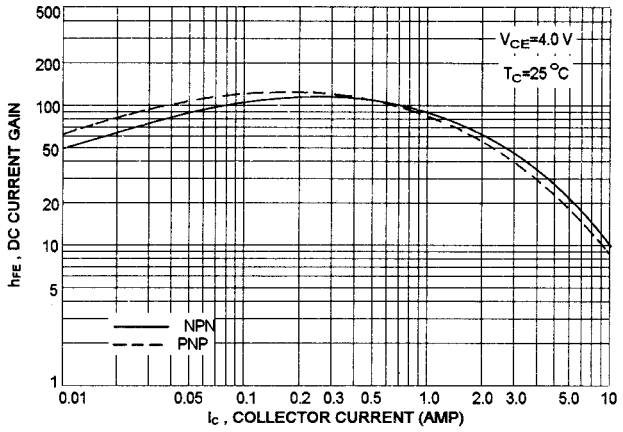
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1) (I_C= 50 mA, I_B= 0)	BD905,BD906 BD907,BD908 BD909,BD910 BD911,BD912	$V_{CEO(sus)}$	45 60 80 100		V
Collector Cutoff Current (V_{CE}= 30 V, I_B= 0) (V_{CE}= 30 V, I_B= 0) (V_{CE}= 40 V, I_B= 0) (V_{CE}= 50 V, I_B= 0)	 BD905,BD906 BD907,BD908 BD909,BD910 BD911,BD912	I_{CEO}		 1.0 1.0 1.0 1.0	mA
Collector Cutoff Current (V_{CB}= 45 V, I_E= 0) (V_{CB}= 60 V, I_E= 0) (V_{CB}= 80 V, I_E= 0) (V_{CB}= 100 V, I_E= 0)	 BD905,BD906 BD907,BD908 BD909,BD910 BD911,BD912	I_{CBO}		 0.5 0.5 0.5 0.5	mA
Emitter Cutoff Current (V_{EB}= 5.0 V, I_C= 0)		I_{EBO}		1.0	mA
ON CHARACTERISTICS (1)					
DC Current Gain (I_C = 0.5 A, V_{CE} = 4.0 V) (I_C = 5.0 A, V_{CE} = 4.0 V) (I_C = 10 A, V_{CE} = 4.0 V)		hFE	 40 15 5.0	 250 150	
Collector-Emitter Saturation Voltage (I_C = 5.0 A, I_B = 0.5 A) (I_C = 10 A, I_B = 2.5 A)		$V_{CE(sat)}$		 1.0 3.0	V
Base-Emitter Saturation Voltage (I_C = 10 A, I_B = 2.5 A)		$V_{BE(sat)}$		2.5	V
Base-Emitter On Voltage (I_C =5.0 A, V_{CE}= 4.0 V)		$V_{BE(on)}$		1.5	V
DYNAMIC CHARACTERISTICS					
Current Gain-Bandwidth Prodct (2) (I_C=500 mA, V_{CE}=4.0 V, f= 1MHz)		f_T	3.0		MHz

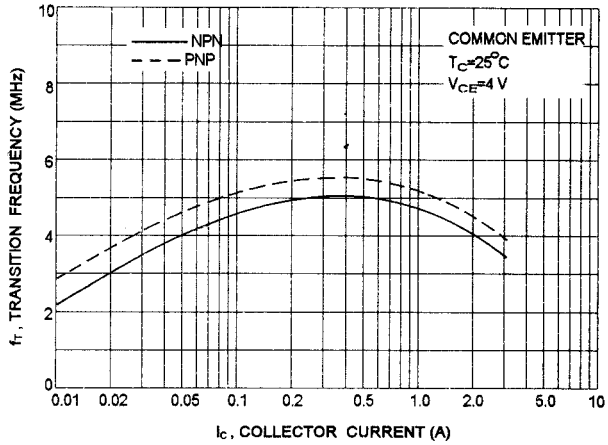
(1) Pulse Test: Pulse width = 300 us , Duty Cycle ≦ 2.0%

(2) $f_T = |h_{fe}| \cdot f_{test}$

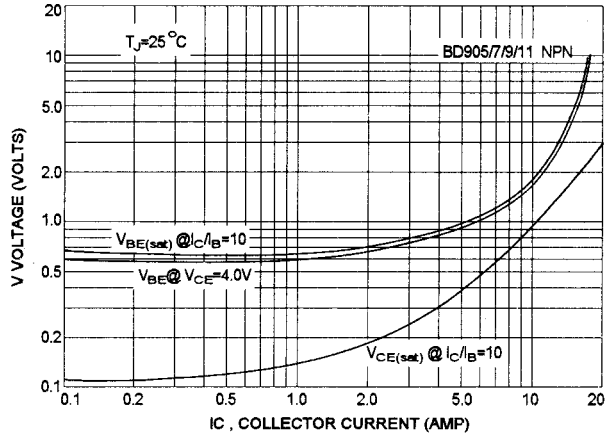
DC CURRENT GAIN



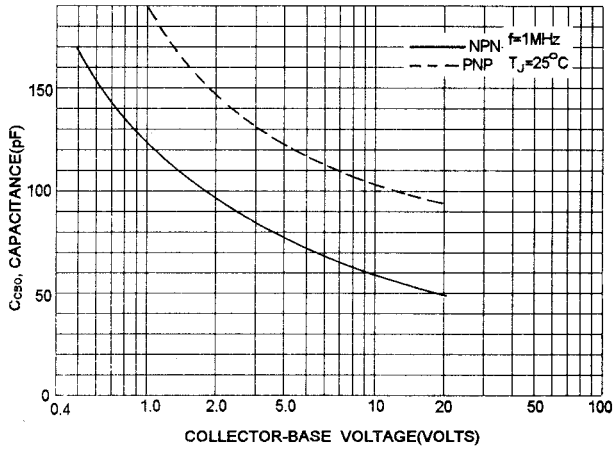
f_T - Ic



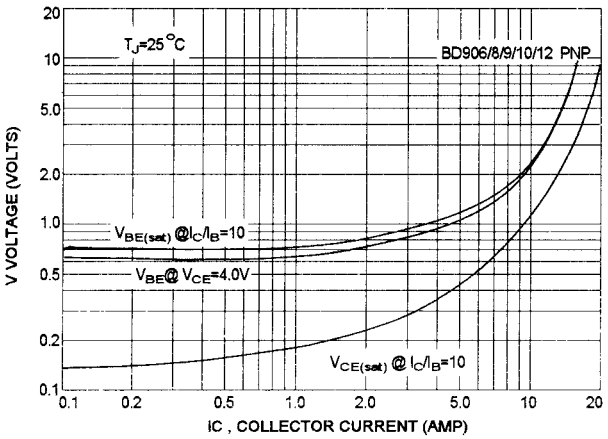
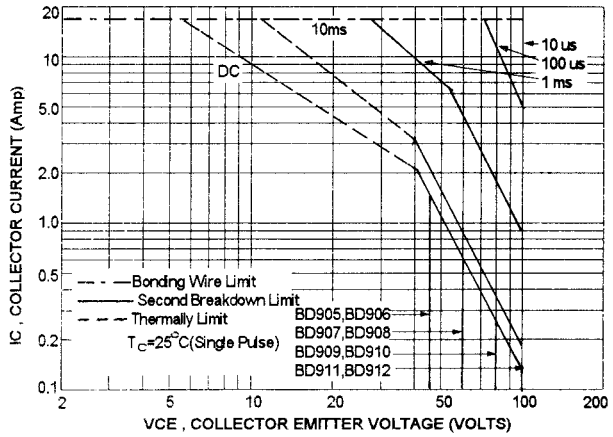
"ON" VOLTAGES



COLLECTOR-BASE CAPACITANCES



"ON" VOLTAGES



ACTIVE REGION SAFE OPERATING AREA(SOA)